

DATASHEET

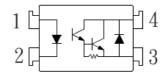
4 PIN DIP HIGH VOLTAGE PHOTODARLINGTON PHOTOCOUPLER EL852 Series



Features:

- •High collector- emitter voltage (VCEO=350V)
- Current transfer ratio (CTR: 1000% min. at I_F =1mA, V_{CE} =2V)
- High isolation voltage between input and output (Viso=5000 V rms)
- Creepage distance >7.62 mm
- Operating temperature up to +100 ℃
- · Compact small outline package
- Pb free and RoHS compliant.
- UL approved
- VDE approved
- SEMKO approved
- NEMKO approved
- · DEMKO approved
- FIMKO approved

Schematic



Pin Configuration

- 1. Anode
- 2. Cathode
- 3. Emitter
- 4. Collector

Description

The EL852 series consists an infrared emitting diodes, optically coupled to a high voltage photo Darlington detector.

It is packaged in a 4-pin DIP package and available in wide-lead spacing and SMD option.

Applications

- Telephone set, telephone exchangers
- Sequence controllers
- System appliances, measuring instruments
- Signal transmission between circuits of different potentials and impedances



Absolute Maximum Ratings (Ta=25℃)

	Parameter	Symbol	Rating	Unit
Input	Forward current	l _F	60	mA
	Peak forward current (1us, pulse)	I _{FP}	1	Α
	Reverse voltage	V _R	6	V
	Power dissipation No derating required up to Ta = 100°C	P_D	100	mW
Output	Power dissipation	р _	300	mW
	Derating factor (above Ta = 80 ℃)	P _C —	5.8	mW/°C
	Collector current	I _C	150	mA
	Collector-Emitter voltage	V_{CEO}	350	V
	Emitter-Collector voltage	V_{ECO}	0.1	V
Total powe	r dissipation	P _{TOT}	320	mW
Isolation v	oltage *1	V _{ISO}	5000	V rms
Operating	temperature	T _{OPR}	-55 ~ +100	∞
Storage te	mperature	T _{STG}	-55 ~ +125	∞
Soldering	Temperature* ²	T _{SOL}	260	∞

Notes:

^{*1} AC for 1 minute, R.H.= $40 \sim 60\%$ R.H. In this test, pins 1 & 2 are shorted together, and pins 3 & 4 are shorted together.

^{*2} For 10 seconds



Electro-Optical Characteristics (Ta=25℃ unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Forward Voltage	V_{F}	-	1.2	1.4	V	I _F = 10mA
Reverse Current	I _R	-	-	10	μΑ	V _R = 4V
Input capacitance	C_in	-	30	250	рF	V = 0, f = 1kHz

Output

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Collector-Emitter dark	I _{CEO}	_	_	200	nA	$V_{CE} = 200V, I_{E} = 0mA$
current	ICEO			200	117 (VGE = 200 V, IF = 01177
Collector-Emitter	BV_CEO	350	_	_	V	$I_{C} = 0.1 \text{mA}$
breakdown voltage	D A CEO	000			v	IC = 0. IIIIA
Emitter-Collector	BV_{ECO}	0.1	_	_	V	I _E = 0.1mA
breakdown voltage	DAFCO	0.1	_	·	V	ie – O. Hillion

Transfer Characteristics

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Current Transfer ratio	CTR	1000	-	15000	%	$I_F = 1 \text{mA}$, $V_{CE} = 2 \text{V}$
Collector-Emitter saturation voltage	V _{CE(sat)}	-	-	1.2	V	I _F = 20mA ,I _C = 100mA
Isolation resistance	R _{IO}	5×10 ¹⁰	-	-	Ω	V _{IO} = 500Vdc, 40∼60% R.H.
Floating capacitance	C_{IO}	-	0.6	1.0	pF	$V_{IO} = 0$, $f = 1MHz$
Cut-off frequency	fc	-	7	-	kHz	V_{CE} = 2V, I_C = 20mA R_L = 100 Ω , -3dB
Rise time	t _r	-	-	300	μs	_ V _{CE} = 2V, I _C = 20mA,
Fall time	t _f	-	-	100	μs	$R_L = 100\Omega$

^{*} Typical values at T_a = 25°C



Typical Electro-Optical Characteristics Curves

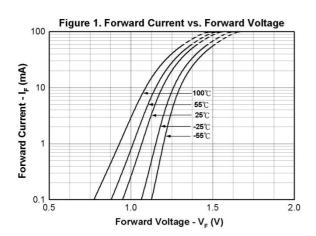


Figure 3. Collector Emitter Saturation Voltage vs.

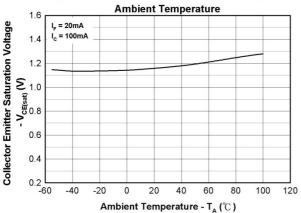


Figure 5. Current Transfer Ratio vs. Forward Current

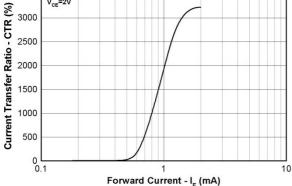


Figure 2. Collector Current vs.

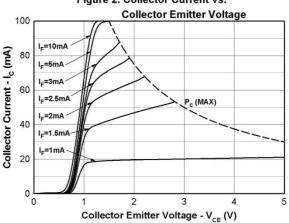


Figure 4. Collector-Emitted Saturation Voltage vs.

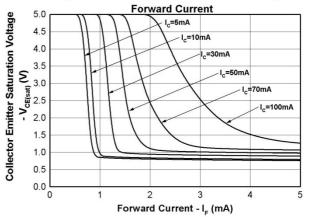


Figure 6. Normalized Current Transfer Ratio vs.

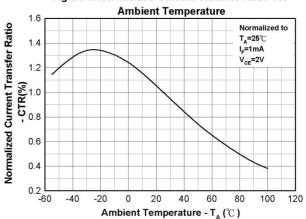
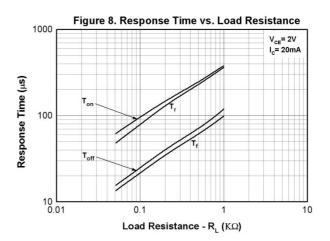
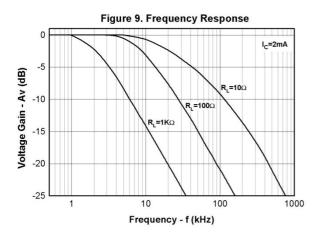


Figure 7. Collector Dark Current vs. **Ambient Temperature** V_{CE}=200V Collector Dark Current - I_{CEO} (nA) 1000 100 10 1 L 90 100 10 20 30 50 60 70 80 Ambient Temperature - T_A (°C)







Order Informatio Part Number

EL852X(Y)-V

Note

X = Lead form option (S, S1, M or none)

Y = Tape and reel option (TA, TB, TU, TD or none).

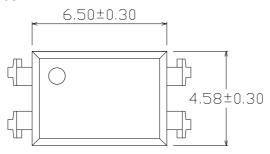
V = VDE safety (optional).

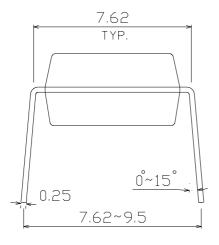
Option	Description	Packing quantity
None	Standard DIP-4	100 units per tube
М	Wide lead bend (0.4 inch spacing)	100 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel
S (TU)	Surface mount lead form + TU tape & reel option	1500 units per reel
S (TD)	Surface mount lead form + TD tape & reel option	1500 units per reel
S1 (TU)	Surface mount lead form (low profile) + TU tape & reel option	1500 units per reel
S1 (TD)	Surface mount lead form (low profile) + TD tape & reel option	1500 units per reel

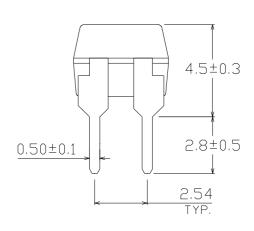


Package Dimension (Dimensions in mm)

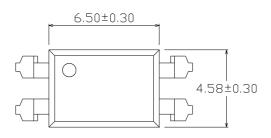
Standard DIP Type

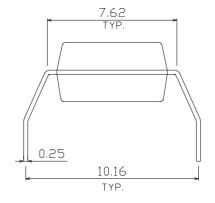


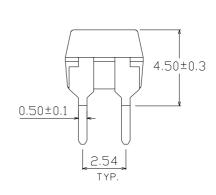




Option M Type

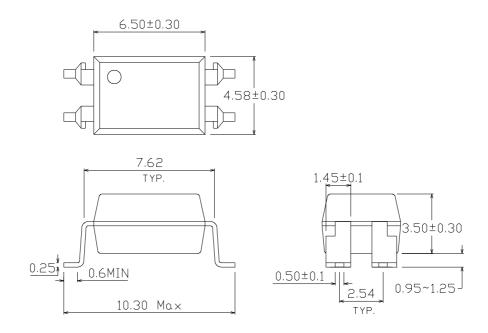




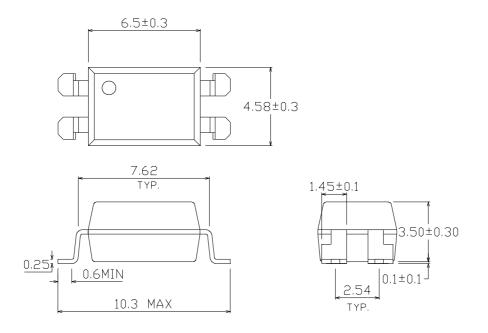




Option S Type

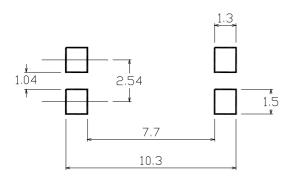


Option S1 Type

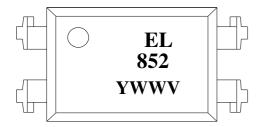




Recommended pad layout for surface mount leadform



Device Marking



Notes

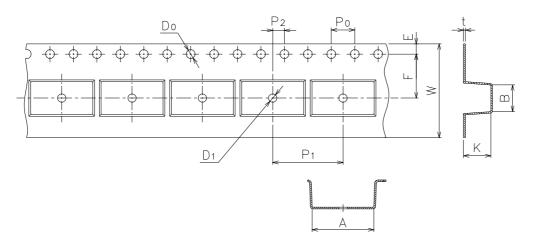
EL denotes EVERLIGHT 852 denotes Device Number Y denotes 1 digit Year code WW denotes 2 digit Week code V denotes VDE optional



Tape & Reel Packing Specifications

Option TA Option TB Option TB Direction of feed from reel

Tape dimensions



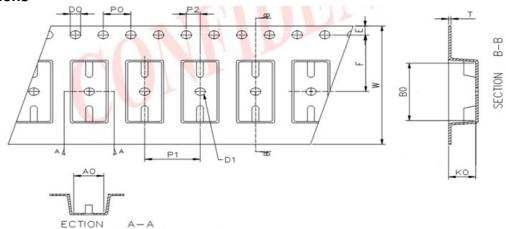
Dimension No.	Α	В	Do	D1	E	F
Dimension (mm) S	10.5±0.1	4.65±0.1	1.5±0.1	1.50±0.1	1.75±0.1	7.5±0.1
Dimension (mm) S1	10.5±0.1	4.65±0.1	1.5±0.1	1.50±0.1	1.75±0.1	7.5±0.1
Dimension No.	Ро	P1	P2	t	w	К
Dimension (mm) S	4.0±0.1	12.0±0.1	2.0±0.1	0.4±0.1	16.0±0.3	5.05±0.1
Dimension (mm) S1	4.0±0.1	12.0±0.1	2.0±0.1	0.4±0.1	16.0±0.3	4.75±0.1



Tape & Reel Packing Specifications

Option TD Option TU Option Tu

Tape dimensions



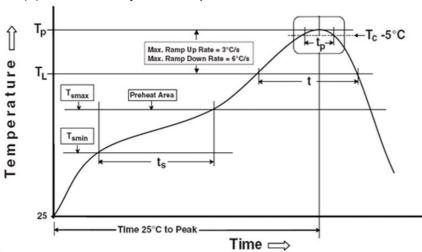
Dimension No.	Ao	Во	Do	D1	E	F
Dimension (mm) S.S1	4.90±0.1	10.40±0.1	1.5±0.1	1.50±0.1	1.75±0.1	7.50±0.1
Dimension No.	Ро	P1	P2	t	W	Ko
Dimension (mm) S.S1	4.00±0.1	8.00±0.	2.00±0.1	0.40±0.1	16.00±0.3	4.60±0.1



Precautions for Use

1. Soldering Condition

1.1 (A) Maximum Body Case Temperature Profile for evaluation of Reflow Profile



Note:

Reference: IPC/JEDEC J-STD-020D

Preheat

Temperature min (T _{smin})	150 ℃
Temperature max (T _{smax})	200℃
Time $(T_{smin} \text{ to } T_{smax}) (t_s)$	60-120 seconds
Average ramp-up rate (T _{smax} to T _p)	3 °C/second max

Other

Other	
Liquidus Temperature (T _L)	217 ℃
Time above Liquidus Temperature (t L)	60-100 sec
Peak Temperature (T _P)	260℃
Time within 5 $^{\circ}$ C of Actual Peak Temperature: T_P - 5 $^{\circ}$ C	30 s
Ramp- Down Rate from Peak Temperature	6°C /second max.
Time 25 ℃ to peak temperature Reflow times	8 minutes max. 3 times



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>>Everlight(亿光)